

AMENDMENTS TO THE SPECIFICATION

Please delete the first and second paragraphs on page 1.

Please insert the following new paragraph as the first paragraph on page 1:

This is a divisional application of Application Serial No. 10/315,394 filed on December 10, 2002.

Please insert the following new paragraph as the second paragraph on page 1:

RELATED APPLICATION

The present invention is related to Application Serial No. 10/315,300 for "MOS Transistor and Method of Forming the Transistor with a Channel Region in a Layer of Composite Material" by Abdalla Aly Naem filed on an even date herewith.

BRIEF DESCRIPTION OF THE DRAWINGS